

## Power MOSFET

**TO-220AB**


N-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Logic-level gate drive
- $R_{DS(on)}$  specified at  $V_{GS} = 4\text{ V}$  and  $5\text{ V}$
- $175\text{ }^{\circ}\text{C}$  operating temperature
- Fast switching
- Ease of paralleling
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


 Available  
**RoHS\***  
 Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### PRODUCT SUMMARY

$V_{DS}$ (V)	100	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 5.0\text{ V}$	0.16
$Q_g$ (Max.) (nC)	28	
$Q_{gs}$ (nC)	3.8	
$Q_{gd}$ (nC)	14	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRL530PbF
Lead (Pb)-free and halogen-free	IRL530PbF-BE3

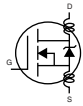

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	100	V	
Gate-source voltage		$V_{GS}$	$\pm 10$		
Continuous drain current	$V_{GS}$ at 5 V	$I_D$	$T_C = 25\text{ }^{\circ}\text{C}$	15	A
			$T_C = 100\text{ }^{\circ}\text{C}$	11	
Pulsed drain current <sup>a</sup>		$I_{DM}$	60		
Linear derating factor			0.59	W/ $^{\circ}\text{C}$	
Single pulse avalanche energy <sup>b</sup>		$E_{AS}$	290	mJ	
Repetitive avalanche current <sup>a</sup>		$I_{AR}$	15	A	
Repetitive avalanche energy <sup>a</sup>		$E_{AR}$	8.8	mJ	
Maximum power dissipation		$P_D$	88	W	
Peak diode recovery dV/dt <sup>c</sup>		dV/dt	5.5	V/ns	
Operating junction and storage temperature range		$T_J, T_{stg}$	-55 to +175	$^{\circ}\text{C}$	
Soldering recommendations (peak temperature) <sup>d</sup>			300 <sup>d</sup>		
Mounting torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 25\text{ V}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 1.9\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 15\text{ A}$  (see fig. 12)
- $I_{SD} \leq 15\text{ A}$ ,  $dI/dt \leq 140\text{ A/ms}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ }^{\circ}\text{C}$
- 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJC}$	-	1.7	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		100	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.14	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		1.0	-	2.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 10$		-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 5.0\text{ V}$	$I_D = 9.0\text{ A}^b$	-	-	0.16	$\Omega$
		$V_{GS} = 4.0\text{ V}$	$I_D = 7.5\text{ A}^b$	-	-	0.22	
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 9.0\text{ A}^b$		6.4	-	-	S
<b>Dynamic</b>							
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$ , see fig. 5		-	930	-	pF
Output capacitance	$C_{oss}$			-	250	-	
Reverse transfer capacitance	$C_{rss}$			-	57	-	
Total gate charge	$Q_g$	$V_{GS} = 5.0\text{ V}$	$I_D = 15\text{ A}, V_{DS} = 80\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	28	nC
Gate-source charge	$Q_{gs}$			-	-	3.8	
Gate-drain charge	$Q_{gd}$			-	-	14	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 50\text{ V}, I_D = 15\text{ A}, R_g = 12\text{ }\Omega, R_D = 32\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	4.7	-	ns
Rise time	$t_r$			-	100	-	
Turn-off delay time	$t_{d(off)}$			-	22	-	
Fall time	$t_f$			-	48	-	
Internal drain inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal source inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	15	A
Pulsed diode forward current <sup>a</sup>	$I_{SM}$			-	-	60	
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 15\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 15\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	150	200	ns
Body diode reverse recovery charge	$Q_{rr}$			-	0.93	1.4	$\mu\text{C}$
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

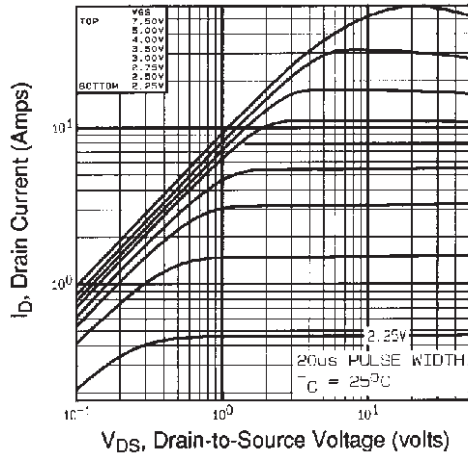


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

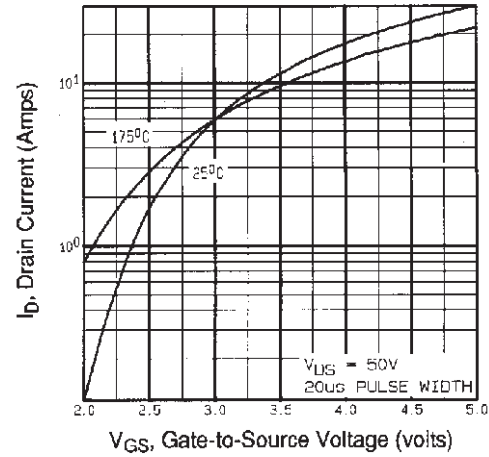


Fig. 3 - Typical Transfer Characteristics

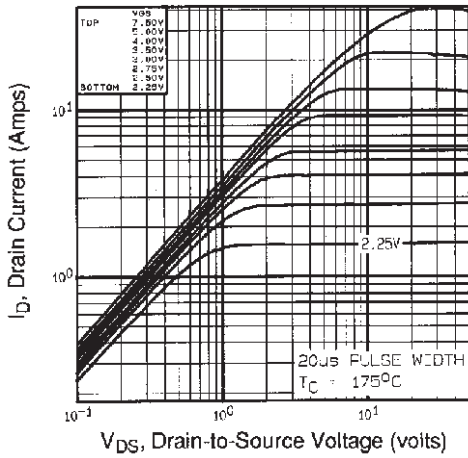


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^\circ\text{C}$

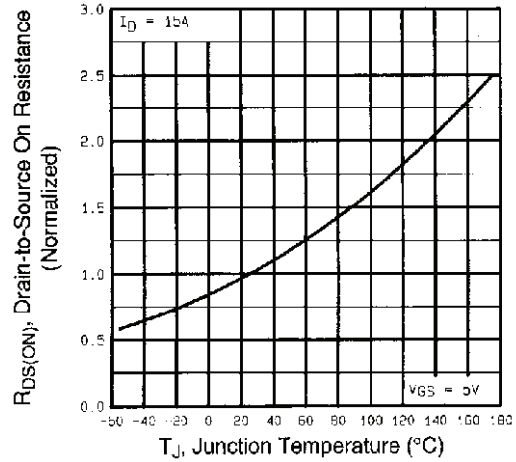


Fig. 4 - Normalized On-Resistance vs. Temperature

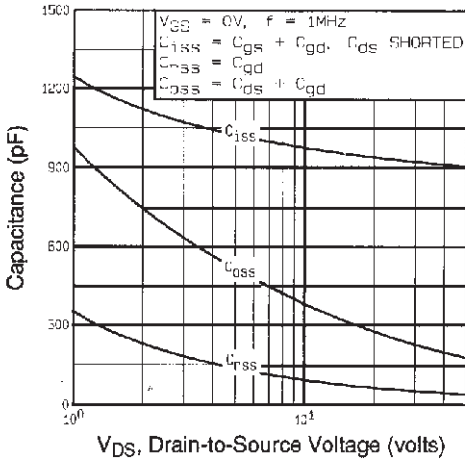


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

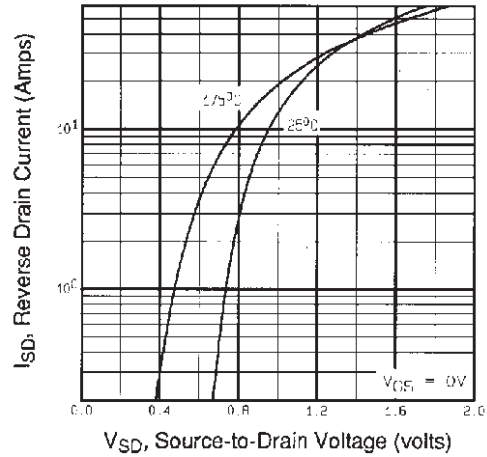


Fig. 7 - Typical Source-Drain Diode Forward Voltage

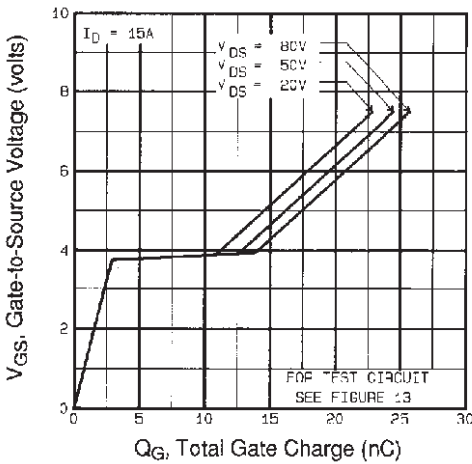


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

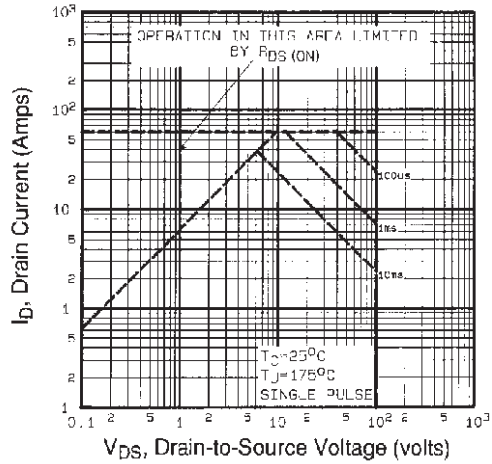


Fig. 8 - Maximum Safe Operating Area

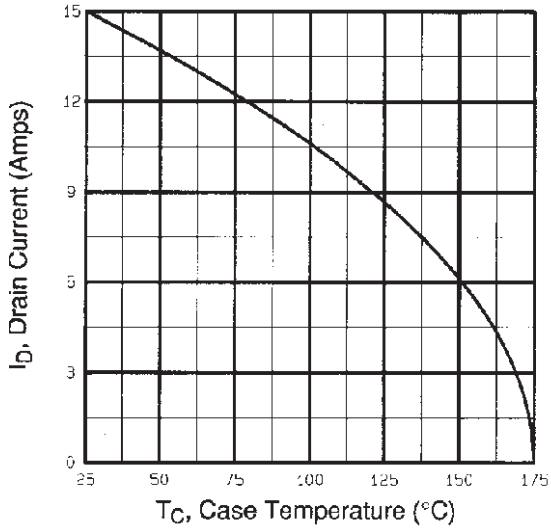


Fig. 9 - Maximum Drain Current vs. Case Temperature

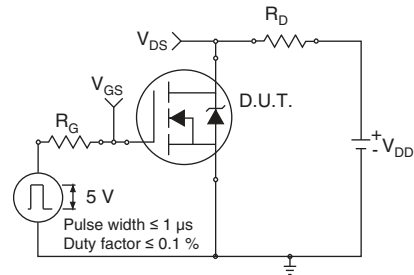


Fig. 10a - Switching Time Test Circuit

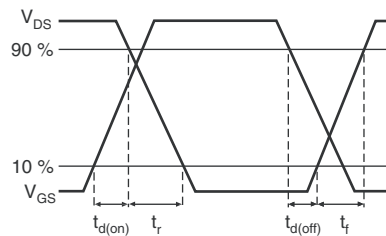


Fig. 10b - Switching Time Waveforms

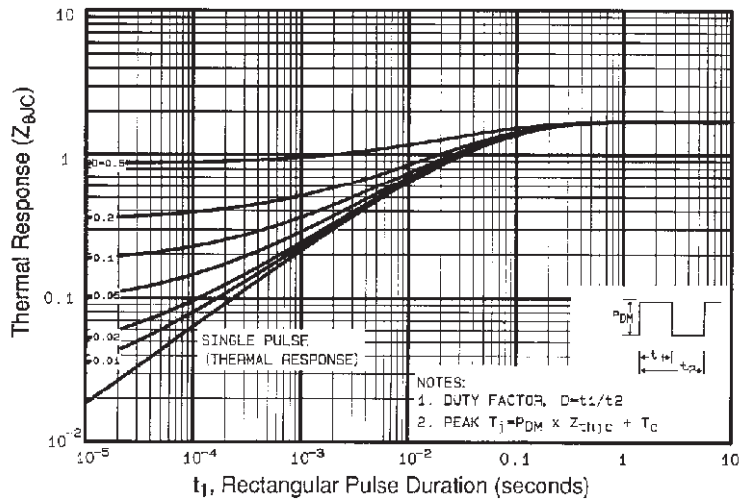


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

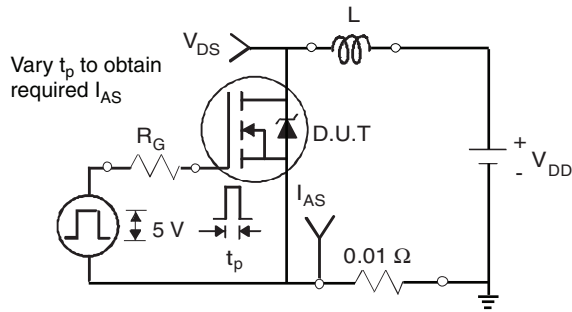


Fig. 12a - Unclamped Inductive Test Circuit

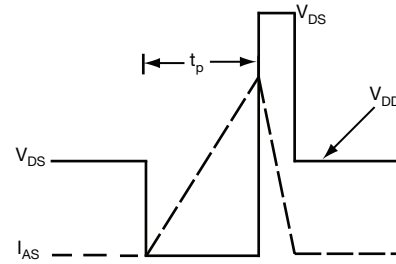


Fig. 12b - Unclamped Inductive Waveforms

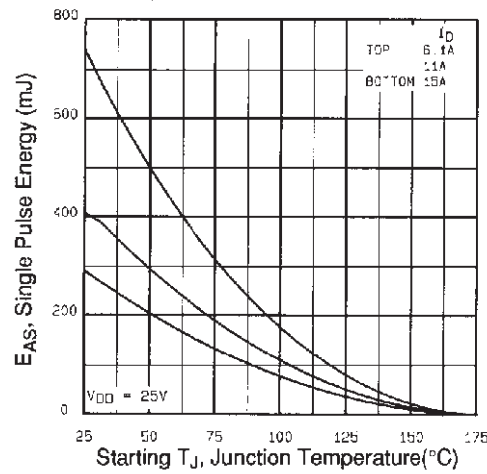


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

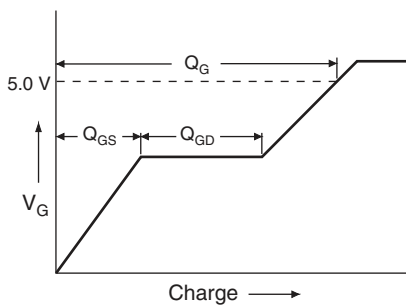


Fig. 13a - Basic Gate Charge Waveform

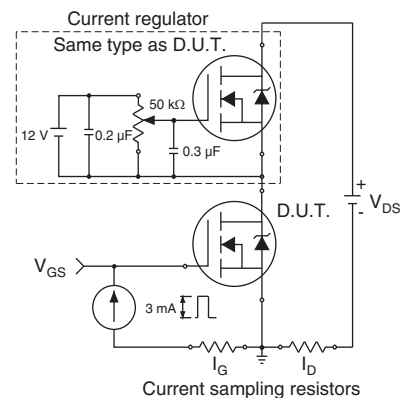
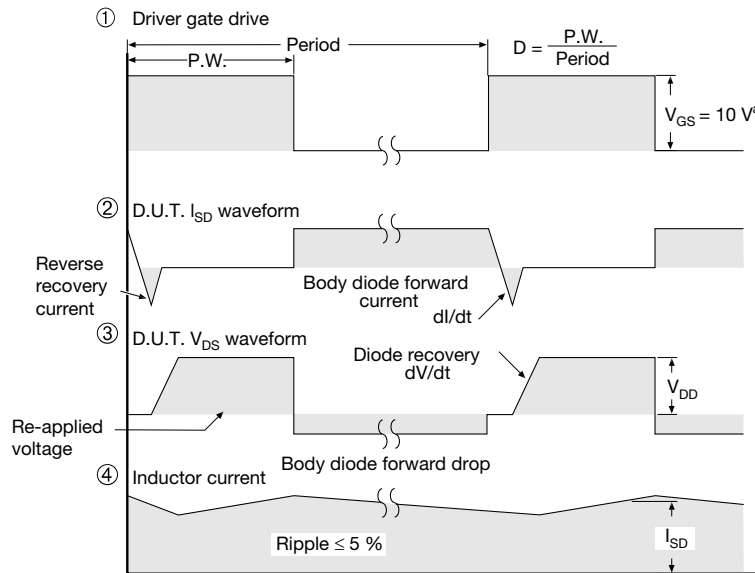
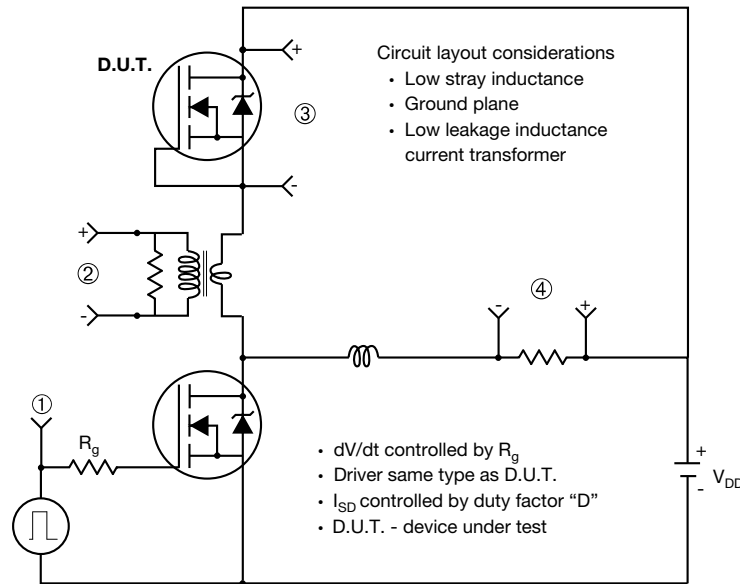


Fig. 13b - Gate Charge Test Circuit

**Peak Diode Recovery dV/dt Test Circuit**



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021  
DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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